



# BUK7Y1R7-40H

N-channel 40 V, 1.7 m $\Omega$  standard level MOSFET in LFPAK56

9 May 2018

Product data sheet

## 1. General description

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Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

## 2. Features and benefits

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- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower  $R_{DSon}$  in same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight  $V_{GS(th)}$  limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
  - Improved reliability, with reduced  $R_{th}$  and  $R_{DSon}$
  - Increases maximum current capability and improved current spreading

## 3. Applications

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- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

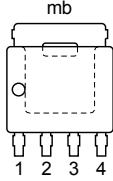
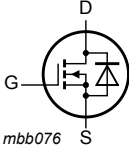
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	40	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$	-	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ <a href="#">Fig. 1</a>	-	-	294	W
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ <a href="#">Fig. 10</a>	0.95	1.35	1.7	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}; V_{DS} = 32\text{ V}; V_{GS} = 10\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	10	25	nC
<b>Source-drain diode</b>						
$Q_r$	recovered charge	$I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 20\text{ V};$ <a href="#">Fig. 16</a>	-	25	-	nC
S	softness factor	$I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 20\text{ V}; T_j = 25\text{ °C};$ <a href="#">Fig. 16</a>	-	0.8	-	

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p><b>LFPAK56; Power-SO8 (SOT669)</b></p>	 <p><i>mbb076</i></p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7Y1R7-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7Y1R7-40H	71H740

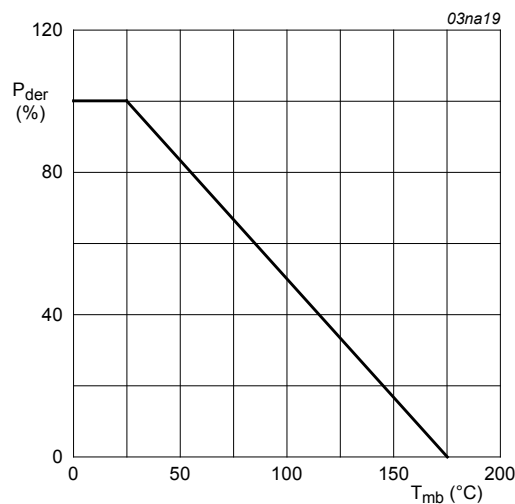
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

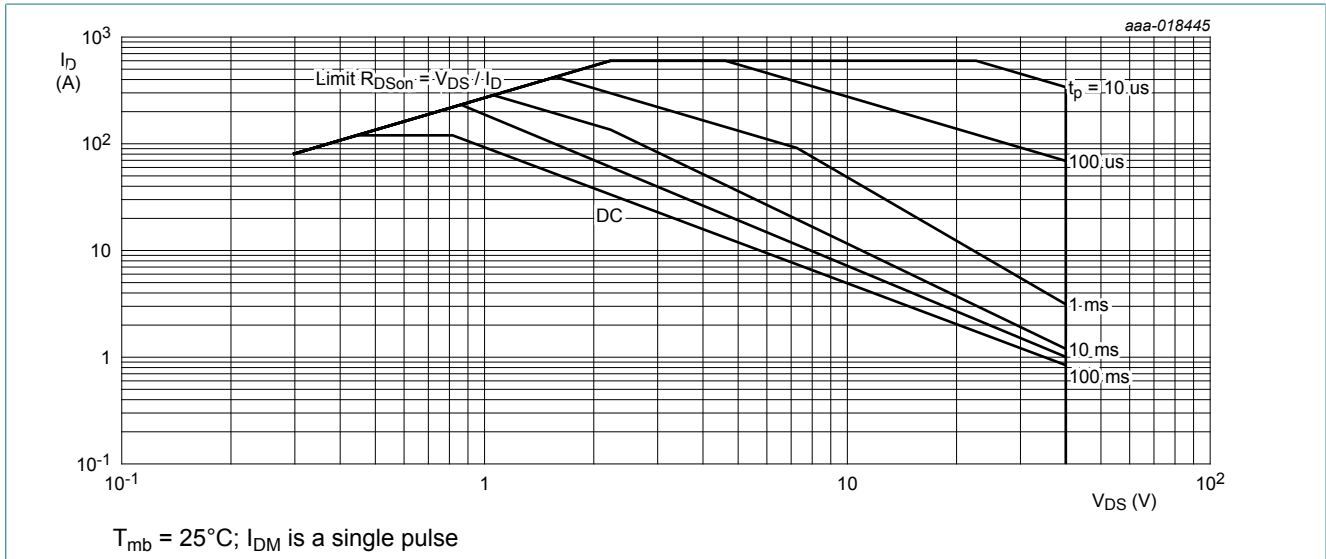
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	40	V
$V_{GS}$	gate-source voltage	DC; $T_j \leq 175\text{ °C}$		-10	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>		-	294	W
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$		-	120	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>		-	600	A
$T_{stg}$	storage temperature			-55	175	°C
$T_j$	junction temperature			-55	175	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	<a href="#">[1]</a>	-	120	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$		-	600	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 120\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped; <a href="#">Fig. 3</a>	<a href="#">[2]</a> <a href="#">[3]</a>	-	158	mJ

- [1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature  
 [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.  
 [3] Refer to application note AN10273 for further information.

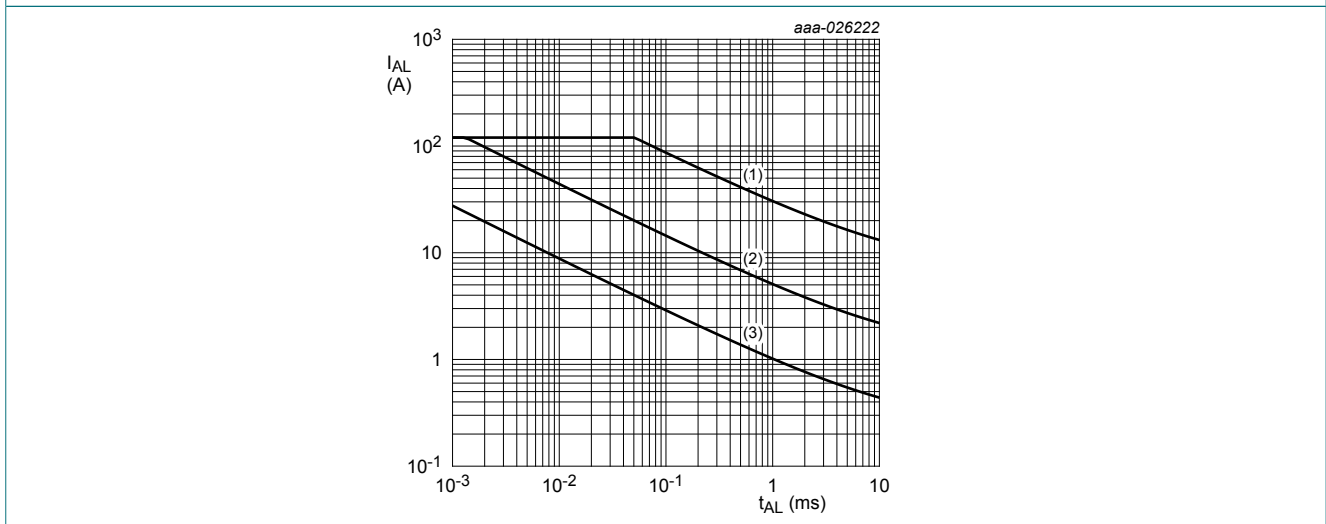


$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**



**Fig. 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

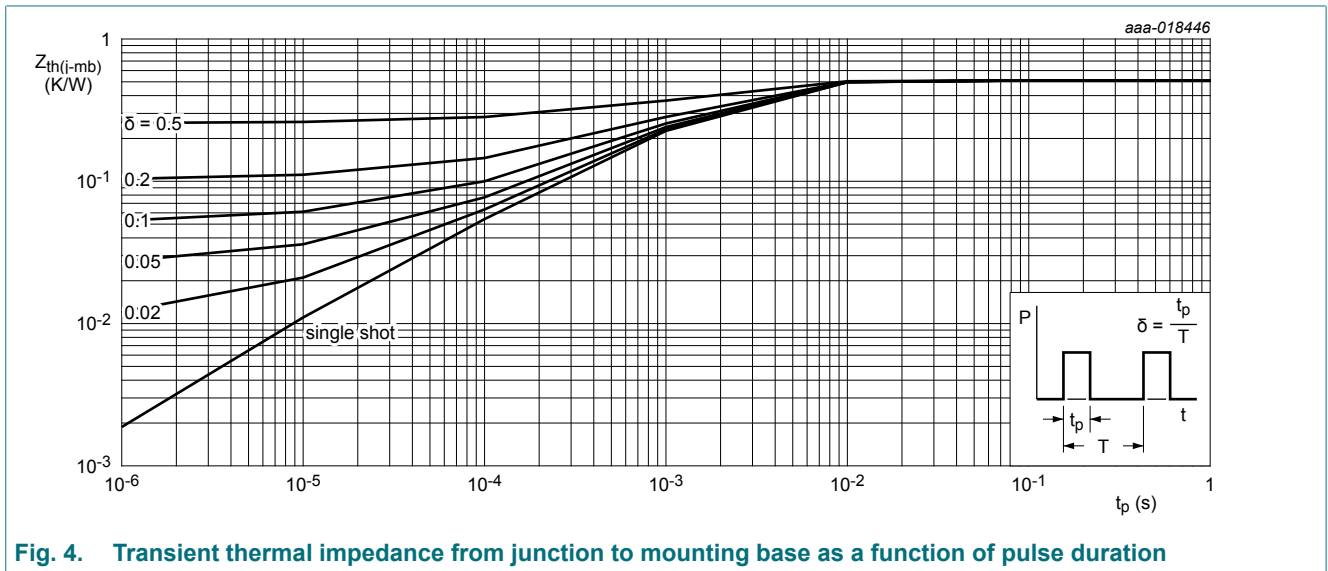


**Fig. 3. Avalanche rating; avalanche current as a function of avalanche time**

## 9. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 4</a>	-	0.39	0.51	K/W



**Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	40	43	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 \text{ }^\circ C$	-	40.5	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	36	40	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 8</a> ; <a href="#">Fig. 9</a>	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$ ; <a href="#">Fig. 8</a>	-	-	4.3	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$ ; <a href="#">Fig. 8</a>	1	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.2	1	$\mu A$
		$V_{DS} = 16 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	1.8	10	$\mu A$
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$	-	200	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 10</a>	0.95	1.35	1.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 105 \text{ }^\circ C$ ; <a href="#">Fig. 11</a>	1.34	2.05	2.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 125 \text{ }^\circ C$ ; <a href="#">Fig. 11</a>	1.48	2.24	3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C$ ; <a href="#">Fig. 11</a>	1.86	2.78	3.7	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	0.4	1.02	2.5	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	56	96	nC
$Q_{GS}$	gate-source charge		-	16	24	nC
$Q_{GD}$	gate-drain charge		-	10	25	nC
$C_{iss}$	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 14</a>	-	4095	6142	pF
$C_{oss}$	output capacitance		-	1083	1516	pF
$C_{rss}$	reverse transfer capacitance		-	178	393	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 10 \text{ V}$ ; $R_{G(ext)} = 5 \text{ } \Omega$	-	14.6	-	ns
$t_r$	rise time		-	12.6	-	ns
$t_{d(off)}$	turn-off delay time		-	35.2	-	ns
$t_f$	fall time		-	16.6	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 15</a>	-	0.8	1.2	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 16</a>	-	32	-	ns
$Q_r$	recovered charge		-	25	-	nC
S	softness factor	$I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a>	-	0.8	-	
		$I_S = 25\text{ A}$ ; $dI_S/dt = -500\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a>	-	0.7	-	

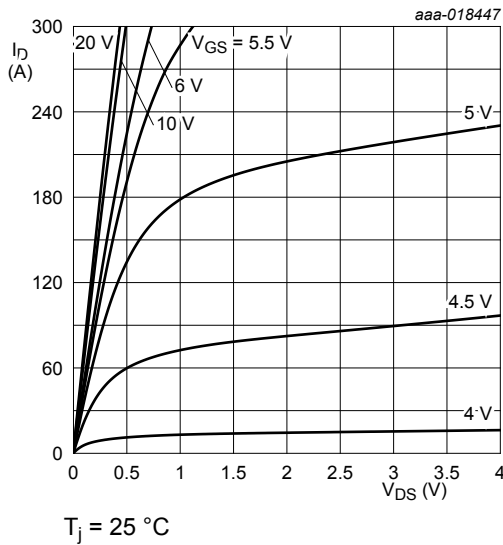


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

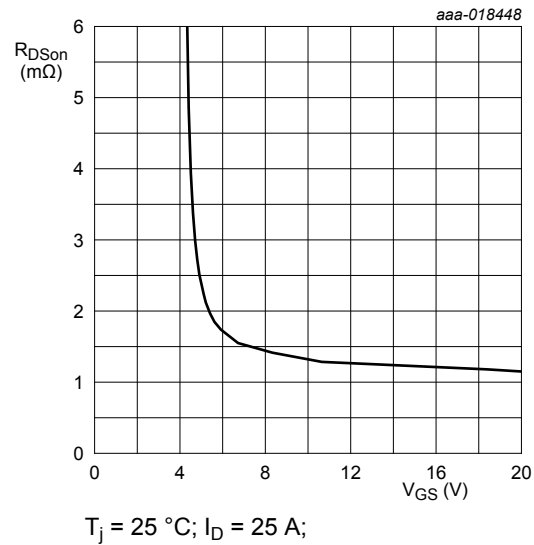


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

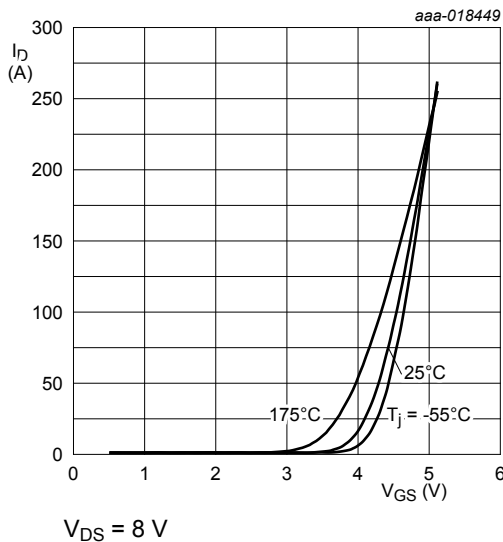


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

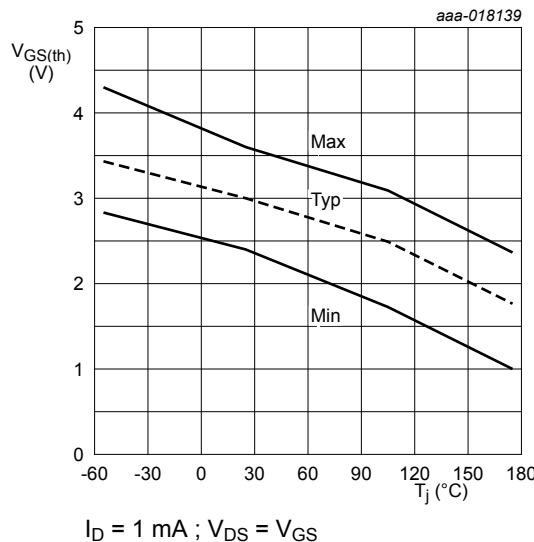
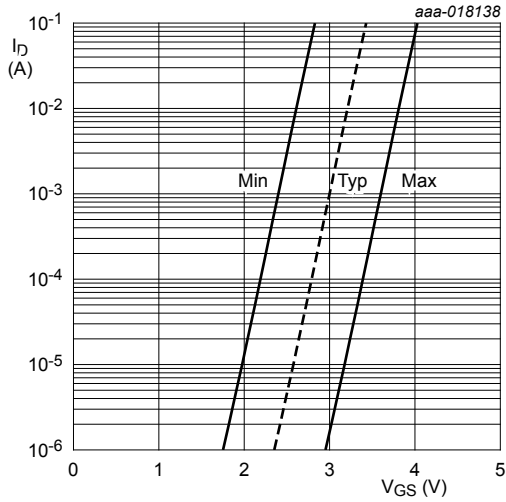


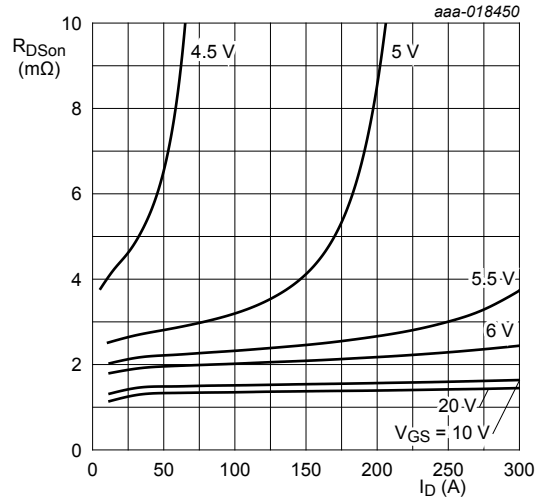
Fig. 8. Gate-source threshold voltage as a function of junction temperature





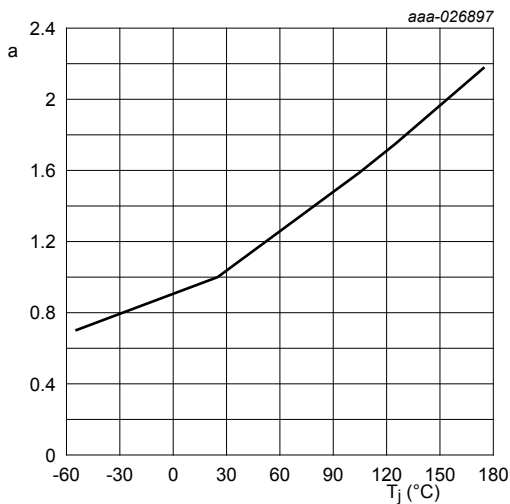
$T_j = 25\text{ °C}; V_{DS} = 5\text{ V}$

Fig. 9. Sub-threshold drain current as a function of gate-source voltage



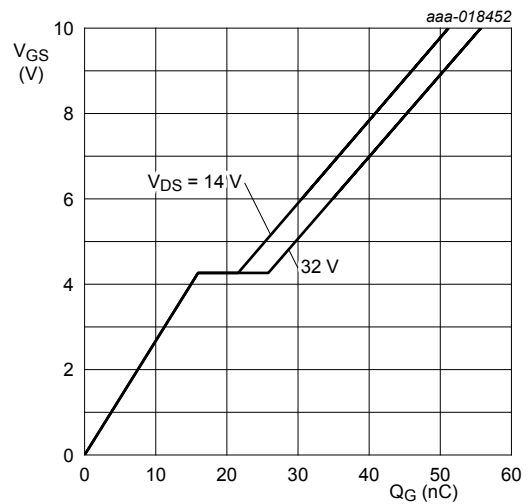
$T_j = 25\text{ °C}$

Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



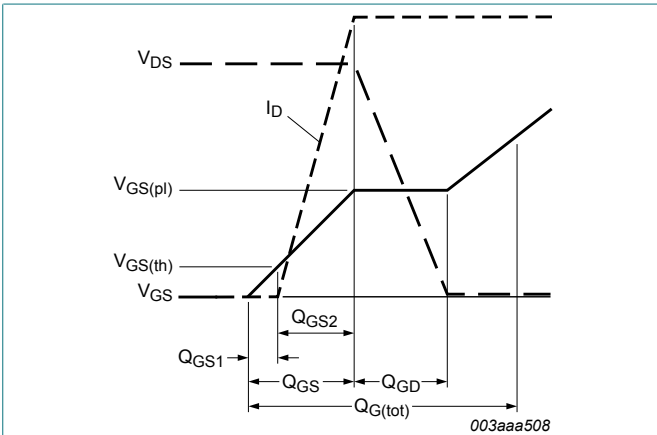
$$a = \frac{R_{DSon}}{R_{DSon}(25\text{ °C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

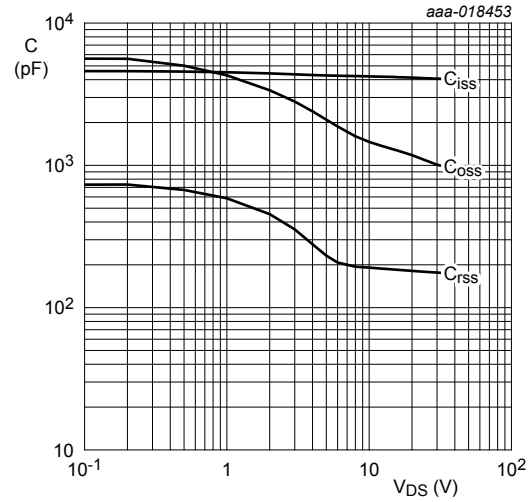


$T_j = 25\text{ °C}; I_D = 25\text{ A}$

Fig. 12. Gate-source voltage as a function of gate charge; typical values

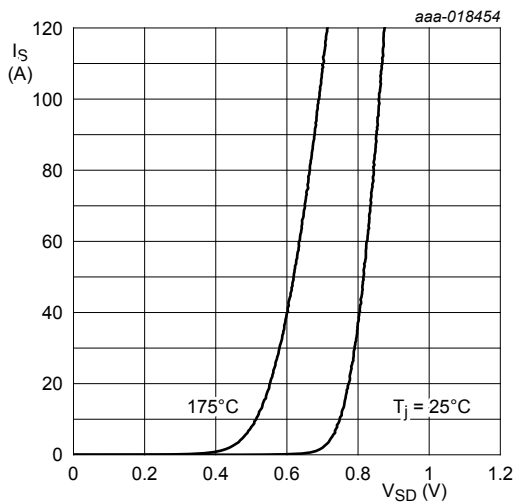


**Fig. 13. Gate charge waveform definitions**



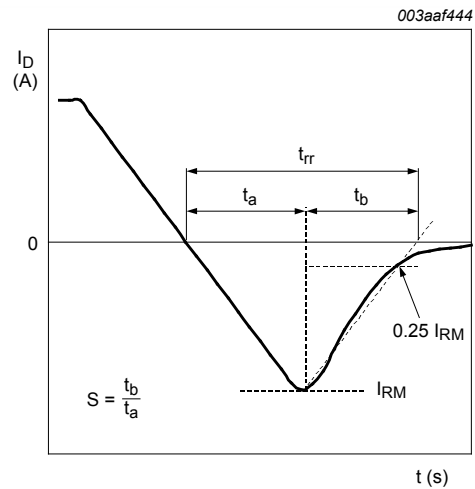
$V_{GS} = 0$  V;  $f = 1$  MHz

**Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



$V_{GS} = 0$  V

**Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



$$t_{rr} = t_a + t_b$$

**Fig. 16. Reverse recovery waveform definitions**

### 11. Package outline

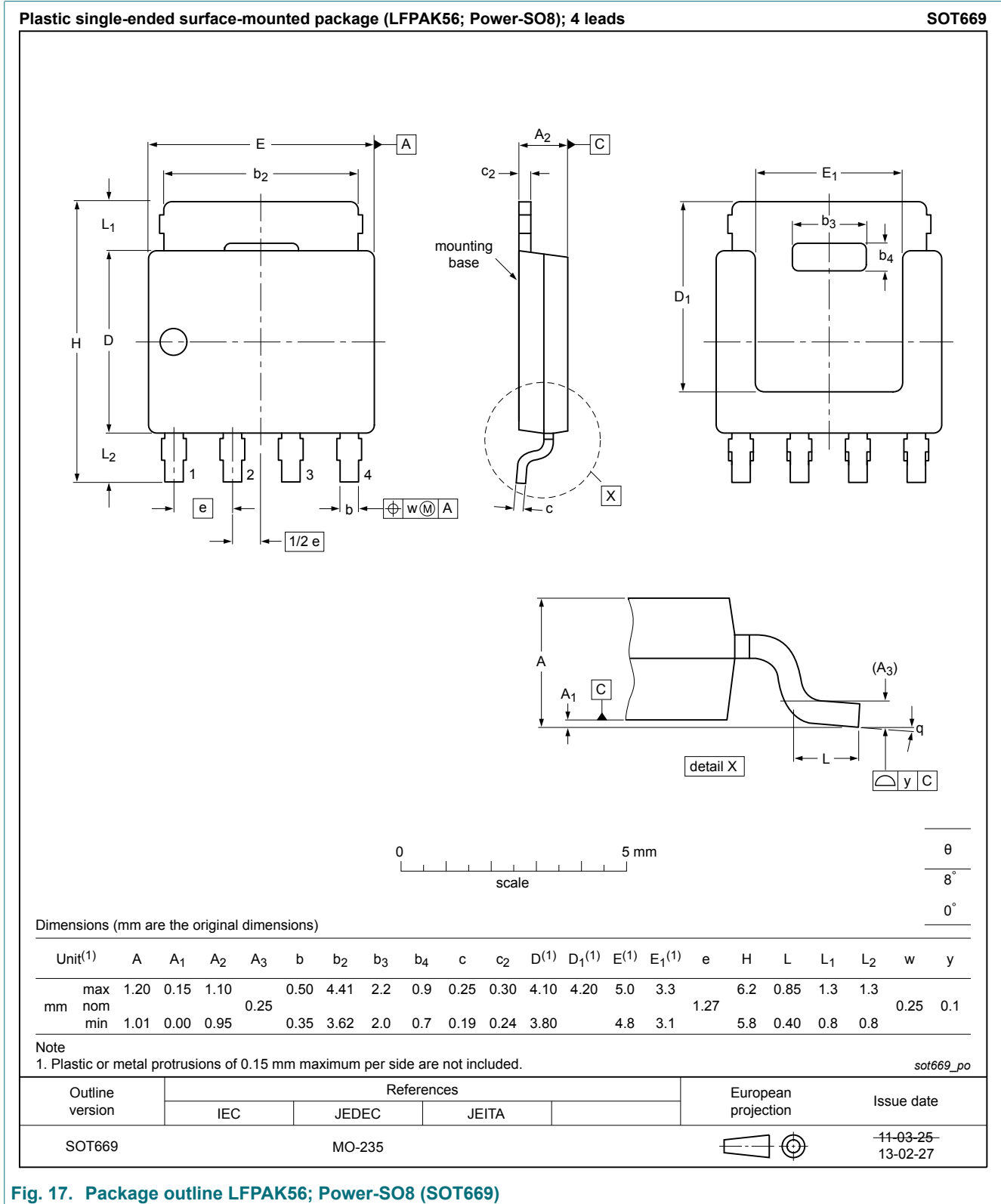


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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